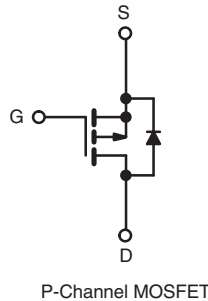
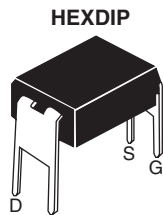


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	- 200	
$R_{DS(on)}$ (Ω)	$V_{GS} = - 10$ V	3.0
Q_g (Max.) (nC)	8.9	
Q_{gs} (nC)	2.1	
Q_{gd} (nC)	3.9	
Configuration	Single	



FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- For Automatic Insertion
- End Stackable
- P-Channel
- Fast Switching
- Ease of Paralleling
- Lead (Pb)-free Available



DESCRIPTION

The Power MOSFETs technology is the key to Vishay advanced line of Power MOSFET transistors. The efficient geometry and unique processing of the Power MOSFETs design achieve very low on-state resistance combined with high transconductance and extreme device ruggedness.

The 4 pin DIP package is a low cost machine-insertable case style which can be stacked in multiple combinations on standard 0.1" pin centers. The dual drain serves as a thermal link to the mounting surface for power dissipation levels up to 1 W.

ORDERING INFORMATION	
Package	HEXDIP
Lead (Pb)-free	IRFD9210PbF SiHFD9210-E3
SnPb	IRFD9210 SiHFD9210



ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	- 200	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	V_{GS} at - 10 V	$T_C = 25$ °C	- 0.40	A
		$T_C = 100$ °C	- 0.25	
Pulsed Drain Current ^a	I_{DM}	- 3.2		
Linear Derating Factor		0.0083	W/°C	
Single Pulse Avalanche Energy ^b	E_{AS}	210	mJ	
Repetitive Avalanche Current ^a	I_{AR}	- 0.40	A	
Repetitive Avalanche Energy ^a	E_{AR}	0.10	mJ	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	1.0	W
Peak Diode Recovery dV/dt^c		dV/dt	- 5.0	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}		- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = - 50$ V, starting $T_J = 25$ °C, $L = 123$ mH, $R_G = 25$ Ω , $I_{AS} = - 1.6$ A (see fig. 12).
- $I_{SD} \leq - 2.3$ A, $dI/dt \leq 70$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	120	°C/W

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$	-	-0.23	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$	-	-	-100	μA
		$V_{DS} = -160\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -0.24\text{ A}^b$	-	-	3.0	Ω
Forward Transconductance	g_{fs}	$V_{DS} = -50\text{ V}, I_D = -0.24\text{ A}$	0.27	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = -25\text{ V},$ $f = 1.0\text{ MHz}$, see fig. 5	-	170	-	pF
Output Capacitance	C_{oss}		-	54	-	
Reverse Transfer Capacitance	C_{rss}		-	16	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V},$ $I_D = -4.0\text{ A}, V_{DS} = -80\text{ V}$ see fig. 6 and 13 ^b	-	-	8.9	nC
Gate-Source Charge	Q_{gs}		-	-	2.1	
Gate-Drain Charge	Q_{gd}		-	-	3.9	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -100\text{ V}, I_D = -2.3\text{ A}$ $R_G = 24\text{ }\Omega, R_D = 41\text{ }\Omega,$ see fig. 10 ^b	-	8.0	-	ns
Rise Time	t_r		-	12	-	
Turn-Off Delay Time	$t_{d(off)}$		-	11	-	
Fall Time	t_f		-	13	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.0	-	nH
Internal Source Inductance	L_S		-	6.0	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	-0.40	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	-3.2	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = -0.40\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	-5.8	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = -2.3\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	110	220	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.56	1.1	μC

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

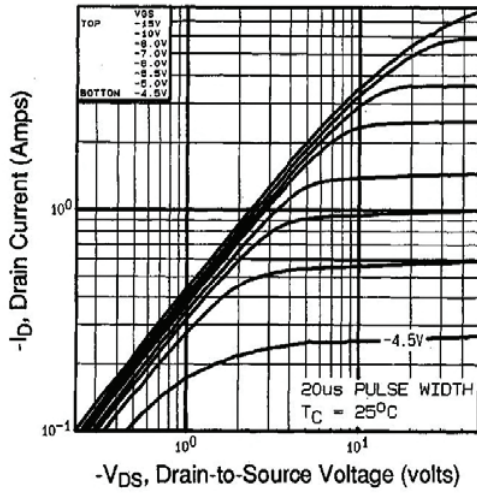


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

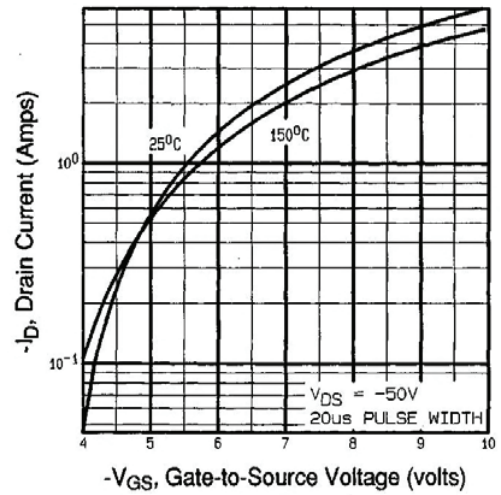


Fig. 3 - Typical Transfer Characteristics

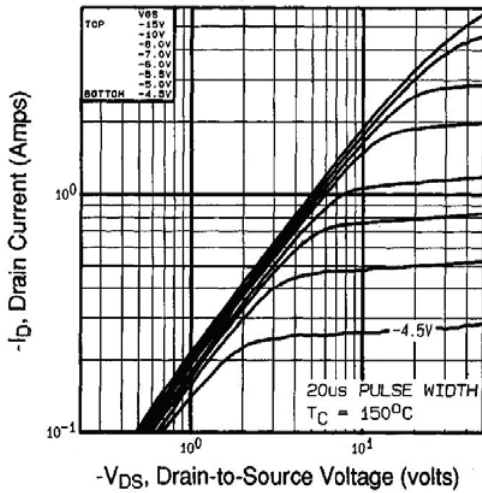


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

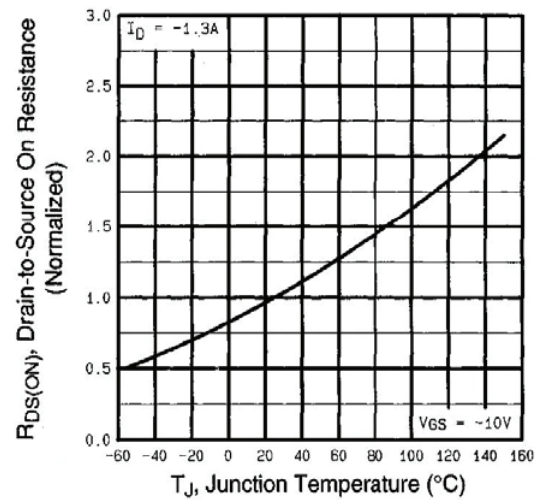


Fig. 4 - Normalized On-Resistance vs. Temperature

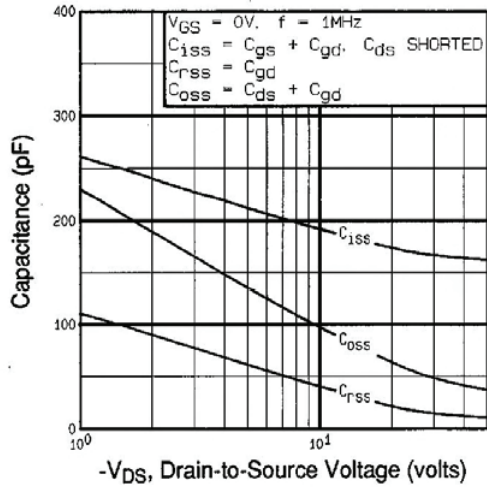


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

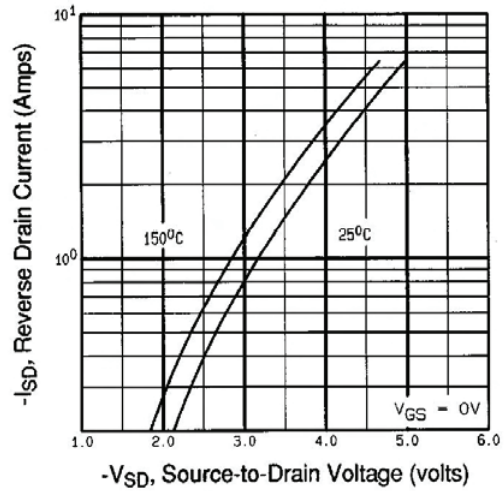


Fig. 7 - Typical Source-Drain Diode Forward Voltage

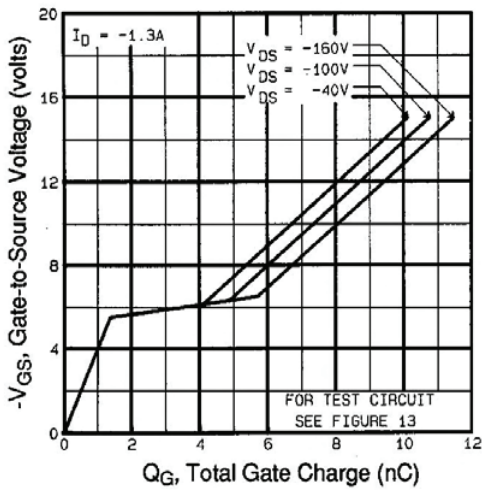


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

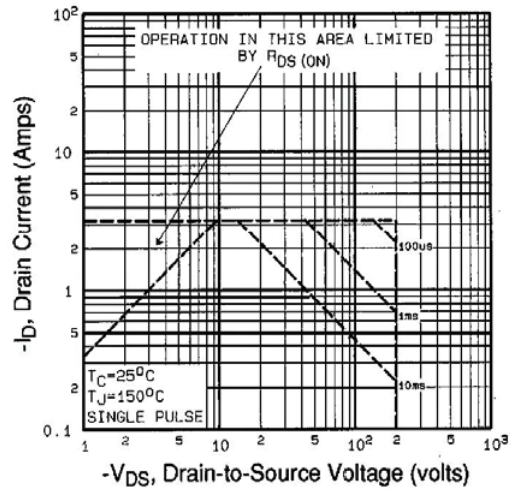


Fig. 8 - Maximum Safe Operating Area

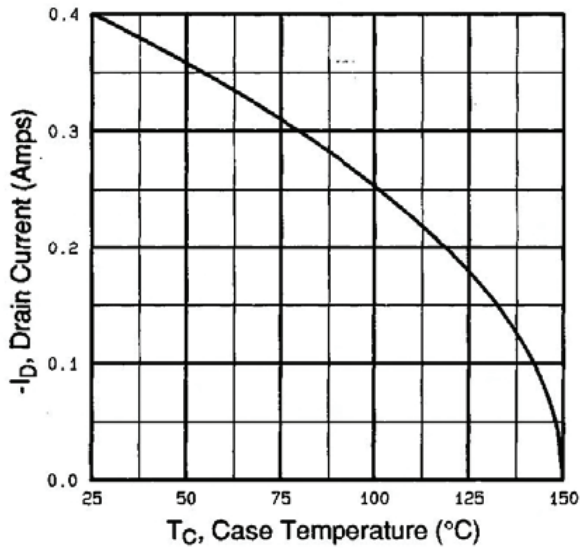


Fig. 9 - Maximum Drain Current vs. Case Temperature

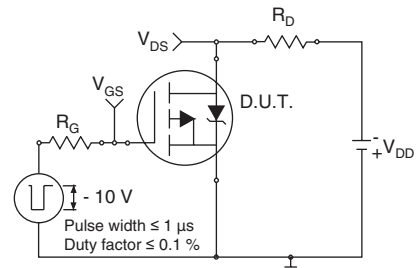


Fig. 10a - Switching Time Test Circuit

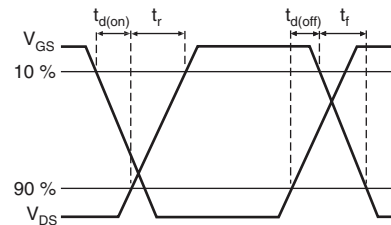


Fig. 10b - Switching Time Waveforms

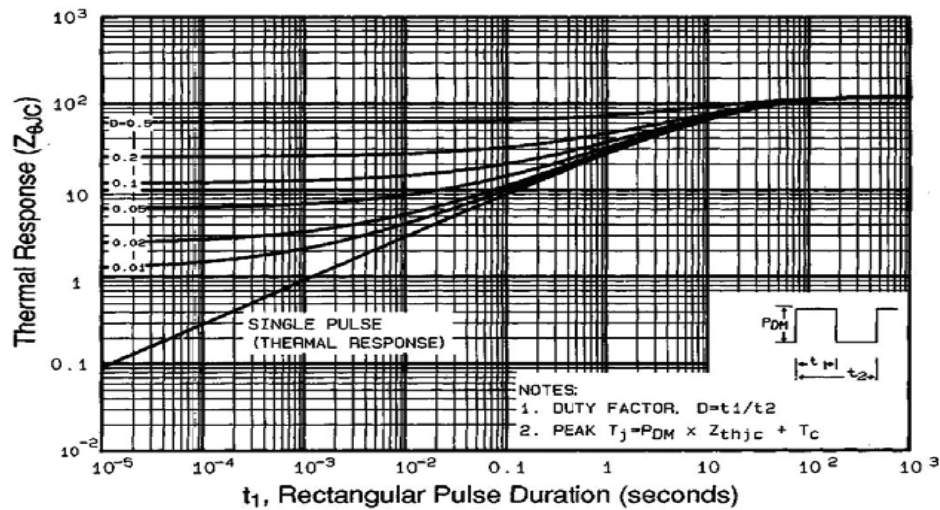


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

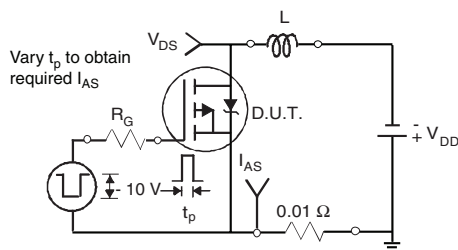


Fig. 12a - Unclamped Inductive Test Circuit

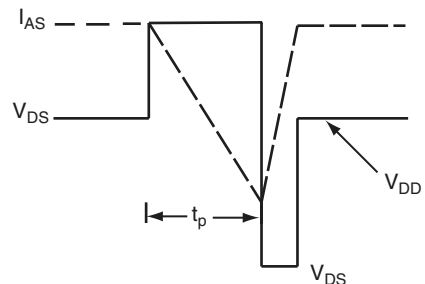


Fig. 12b - Unclamped Inductive Waveforms

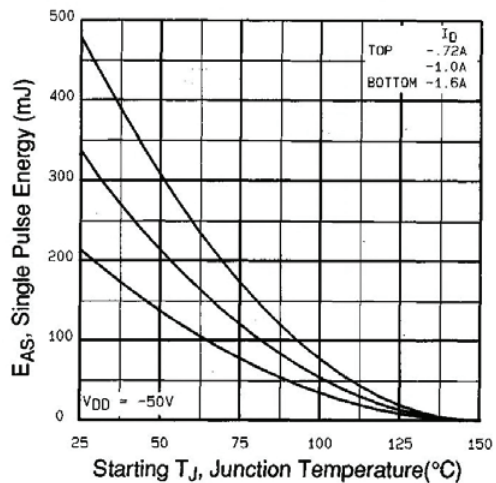


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

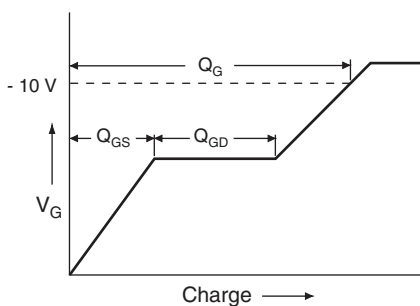


Fig. 13a - Basic Gate Charge Waveform

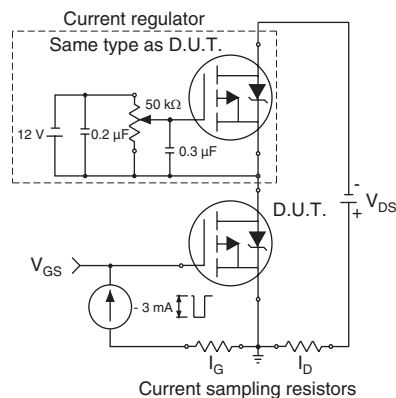
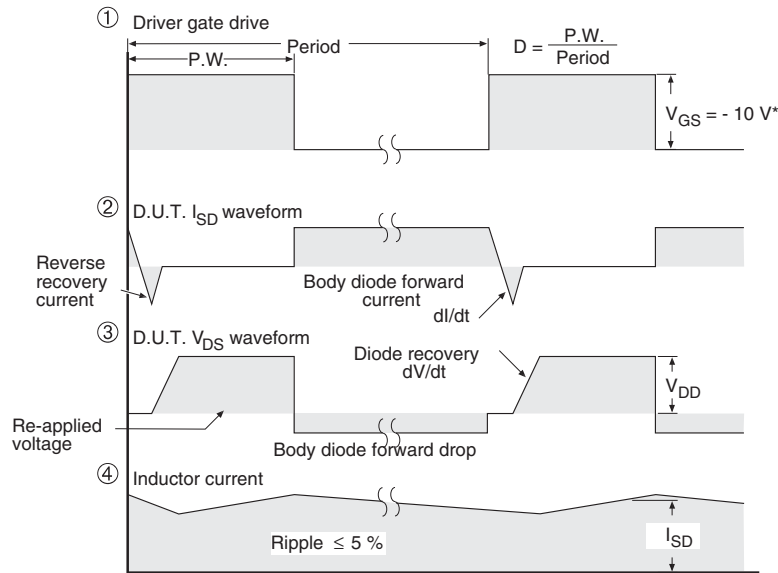
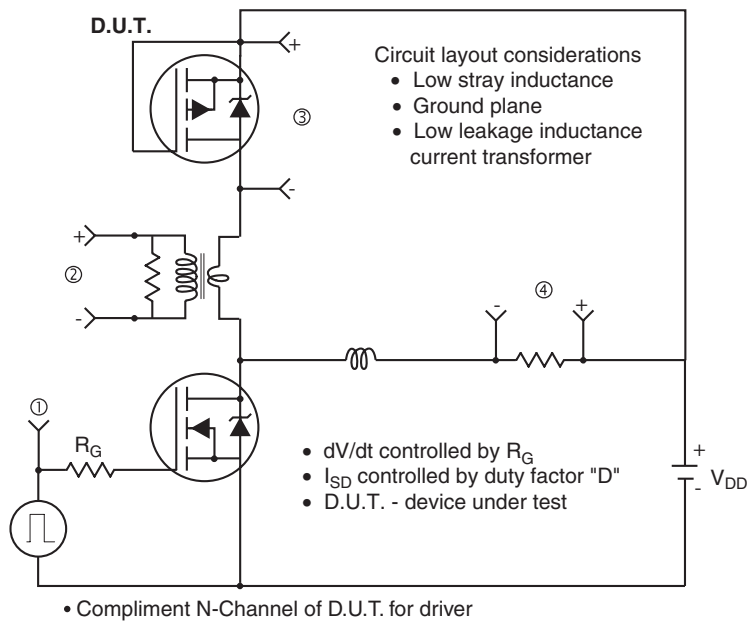


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = -5 V$ for logic level and $-3 V$ drive devices

Fig. 14 - For P-Channel

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